

## N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- Advanced trench cell design
- Super Trench MOSFET
- Low Thermal Resistance

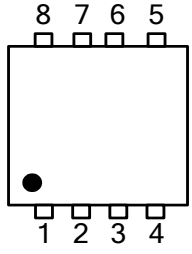
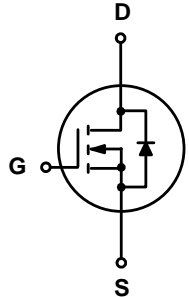
#### 1.2 Applications

- Motor drivers
- DC - DC Converter

#### 1.3 Quick reference

- $BV \geq 30\text{ V}$
- $P_{tot} \leq 20.8\text{ W}$
- $I_D \leq 71\text{ A}$
- $R_{DS(ON)} \leq 2.7\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- $R_{DS(ON)} \leq 3.8\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$

### 2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 <p>Top View DFN3.3x3.3-8L</p>	
4	Gate		
5,6,7,8	Drain		



### 3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	Drain-Source Voltage	T <sub>C</sub> = 25 °C	30	-	V
V <sub>GS</sub>	Gate-Source Voltage	T <sub>C</sub> = 25 °C	-	± 20	V
I <sub>D</sub> *	Drain Current ( DC )	T <sub>C</sub> = 25 °C, V <sub>GS</sub> = 10 V	-	71	A
		T <sub>C</sub> = 100 °C, V <sub>GS</sub> = 10 V	-	45	A
I <sub>DM</sub> *,**,***	Drain Current ( Pulsed )	T <sub>C</sub> = 25 °C, V <sub>GS</sub> = 10 V	-	160	A
P <sub>tot</sub> *	Total Power Dissipation	T <sub>C</sub> = 25 °C	-	20.8	W
T <sub>stg</sub>	Storage Temperature		- 55	150	°C
T <sub>J</sub>	Junction Temperature		-	150	°C
I <sub>S</sub>	Diode Forward Current	T <sub>C</sub> = 25 °C	-	71	A
E <sub>AS</sub> *	Single Pulsed Avalanche Energy	V <sub>DD</sub> = 30 V , L= 1 mH	-	312	mJ
R <sub>θJA</sub> *	Thermal Resistance- Junction to Ambient		-	62.5	°C / W
R <sub>θJC</sub> *	Thermal Resistance- Junction to Case		-	6	

Notes :

- \* Surface Mounted on 1 in<sup>2</sup> pad area, t ≤ 10 sec
- \*\* Pulse width ≤ 300 μs, duty cycle ≤ 2 %
- \*\*\* Limited by bonding wire

### 4. Marking Information

Product Name	Marking
KJ0203QB	<div style="display: inline-block; background-color: black; color: white; padding: 2px;">0203 YWWXXX</div> YWWXXX: Date Code

### 5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ0203QB	DFN3.3*3.3			5000	

Note: KUAJIJIXIN defines " Green " as lead-free ( RoHS compliant ) and halogen free ( Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C )



快捷冠

# KJ0203QB

## 6. Electrical Characteristics (T<sub>A</sub> = 25 °C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30	-	-	V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = 250 μA	1	-	2	V
I <sub>DSS</sub>	Zero Gate Voltage Source Current	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		T <sub>J</sub> = 85 °C	-	-	30	μA
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> = ± 20 V, V <sub>DS</sub> = 0 V	-	-	± 100	nA
R <sub>DS(ON)</sub> <sup>a</sup>	Drain-Source On-State Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	2.2	2.7	mΩ
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	2.9	3.8	
<b>Diode Characteristics</b>						
V <sub>SD</sub> <sup>a</sup>	Diode Forward Voltage	I <sub>SD</sub> = 20 A, V <sub>GS</sub> = 0 V	-	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>SD</sub> = 20 A, dI <sub>SD</sub> /dt = 100 A/μs	-	42	-	nS
Q <sub>rr</sub>	Reverse Recovery Charge		-	35	-	nC
<b>Dynamic Characteristics<sup>b</sup></b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 15 V Frequency = 1 MHz	-	2293	-	pF
C <sub>oss</sub>	Output Capacitance		-	1210	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	100	-	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> = 15 V, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 4.5 Ω, R <sub>L</sub> = 0.75 Ω, I <sub>DS</sub> = 20 A	-	8.5	-	nS
t <sub>r</sub>	Turn-on Rise Time		-	52	-	
t <sub>d(off)</sub>	Turn-off Delay Time		-	41	-	
t <sub>f</sub>	Turn-off Fall Time		-	27	-	
<b>Gate Charge Characteristics<sup>b</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>DS</sub> = 20 A	-	41	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	8.2	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	7.2	-	

Notes :

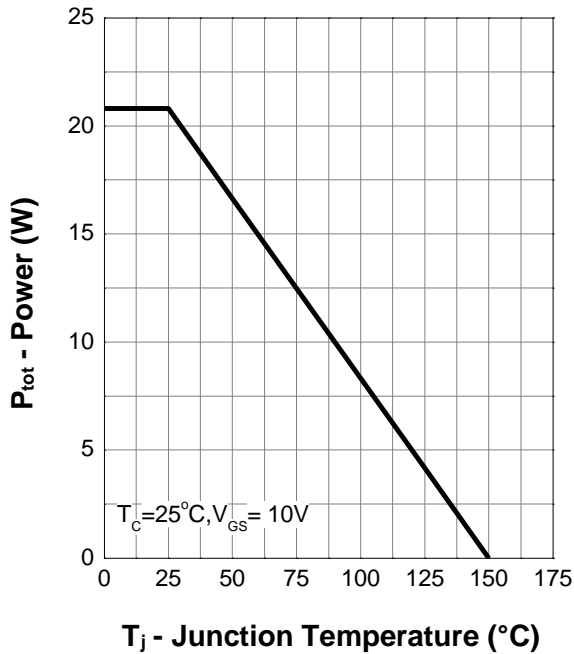
a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2 %

b : Guaranteed by design, not subject to production testing

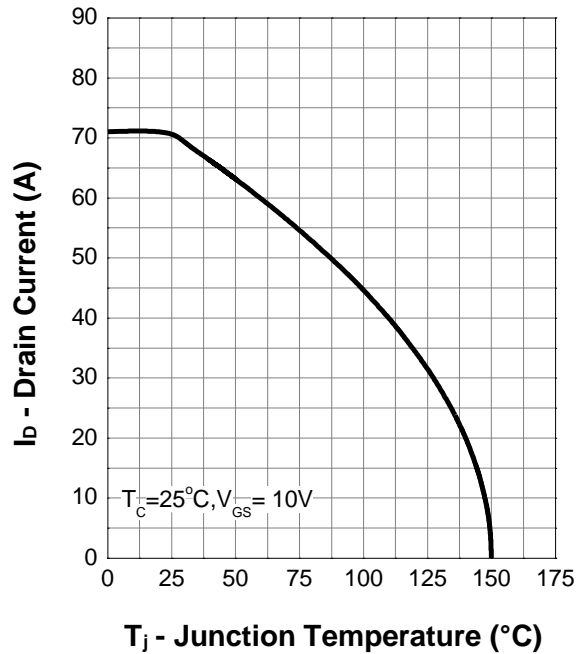


### 7. Typical Characteristics (Cont.)

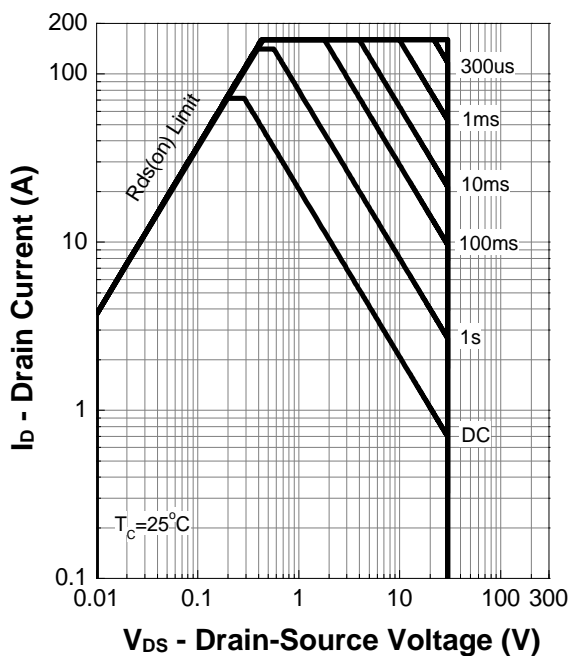
Power Capability



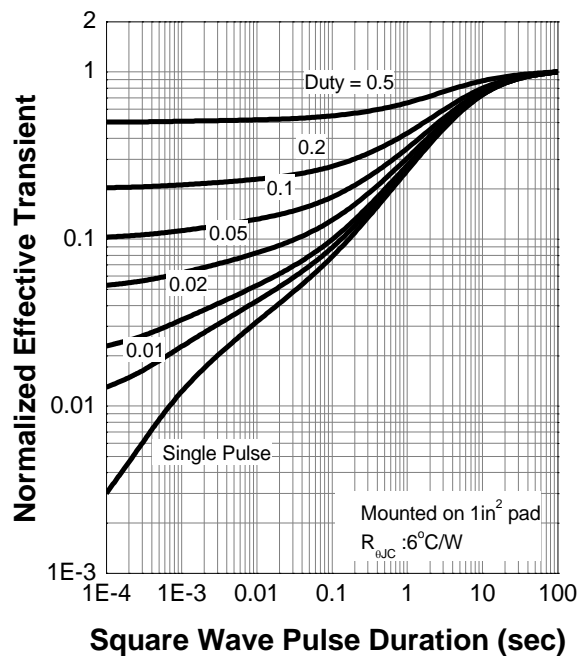
Current Capability



Safe Operation Area



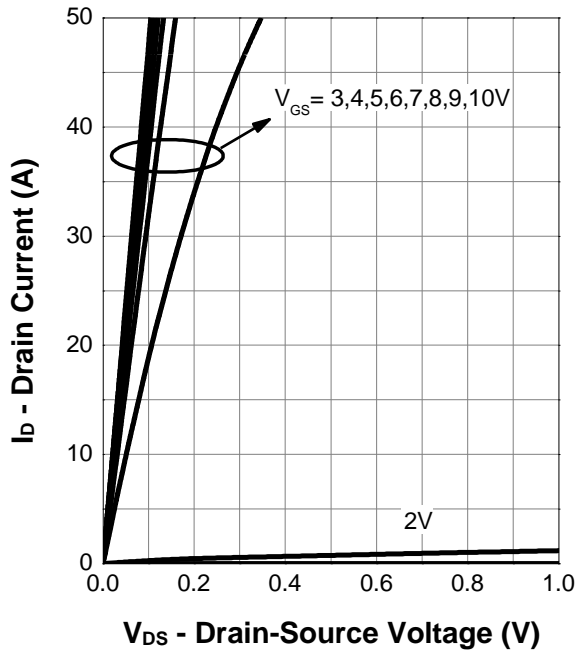
Transient Thermal Impedance



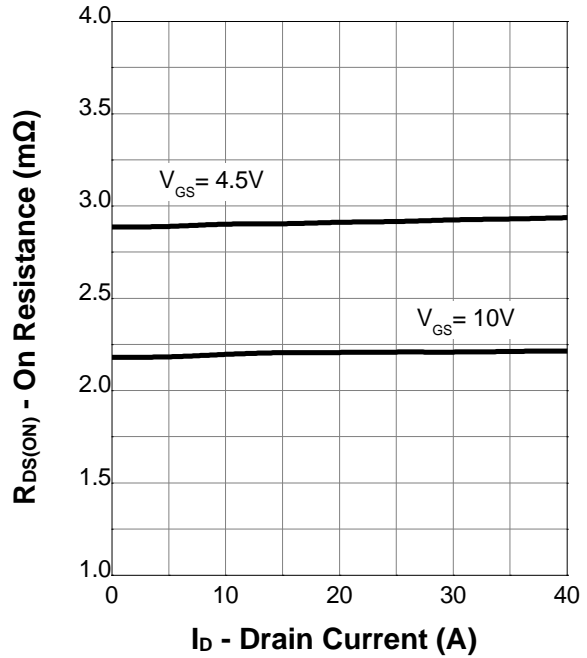


### 7. Typical Characteristics (Cont.)

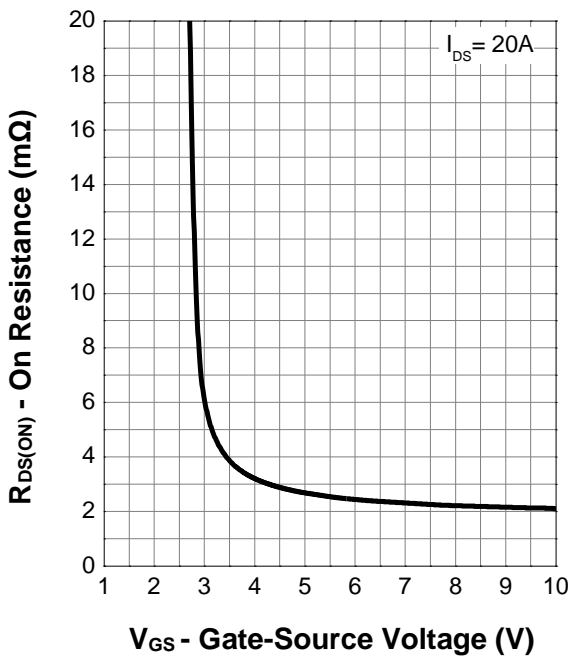
Output Characteristics



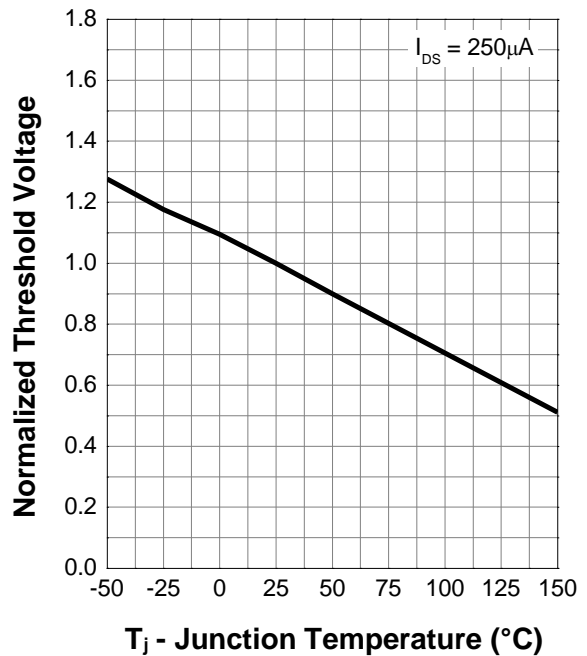
On Resistance



Transfer Characteristics



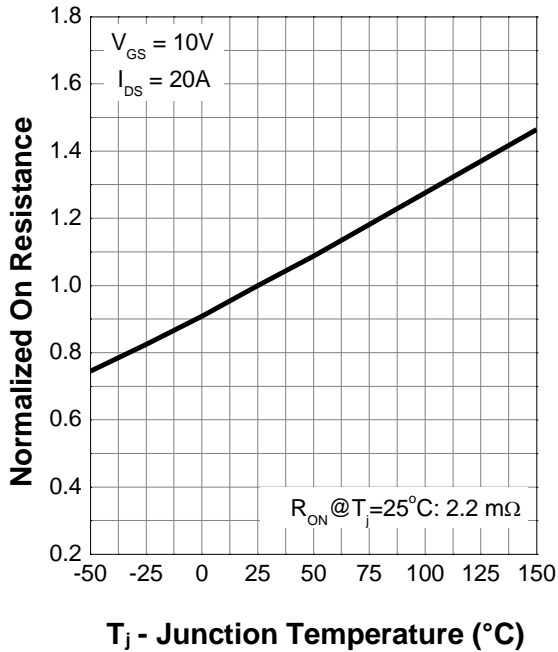
Normalized Threshold Voltage



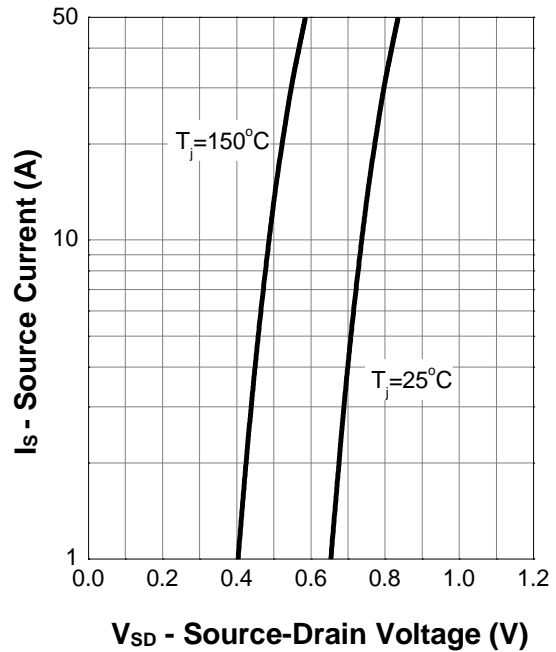


### 7. Typical Characteristics (Cont.)

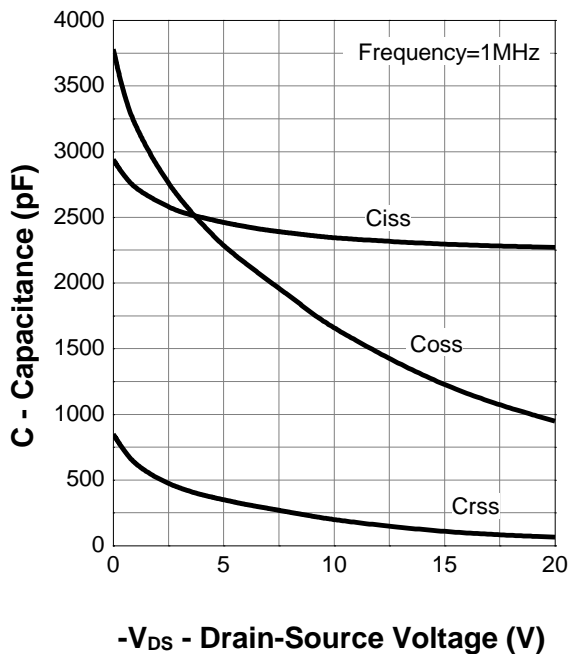
Normalized On Resistance



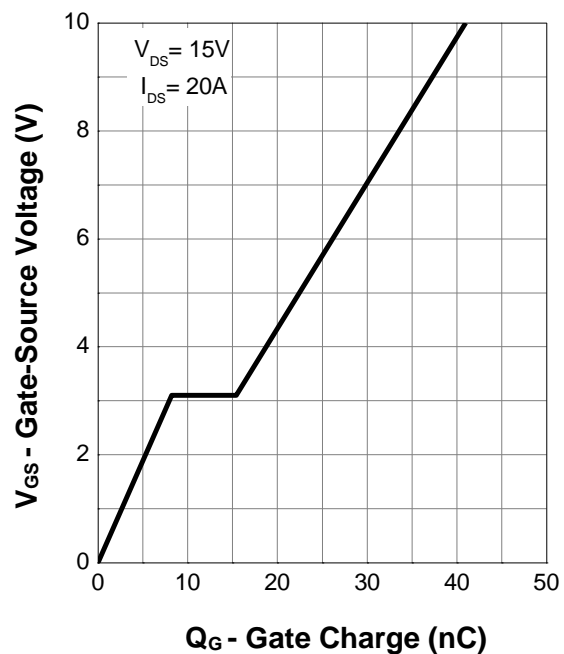
Diode Forward Current



Capacitance



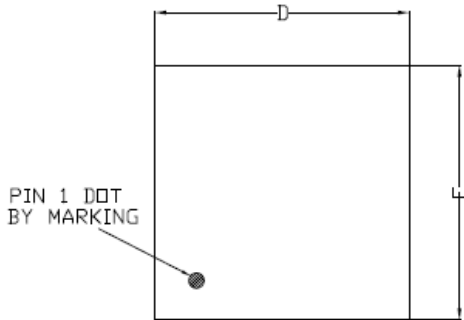
Gate Charge



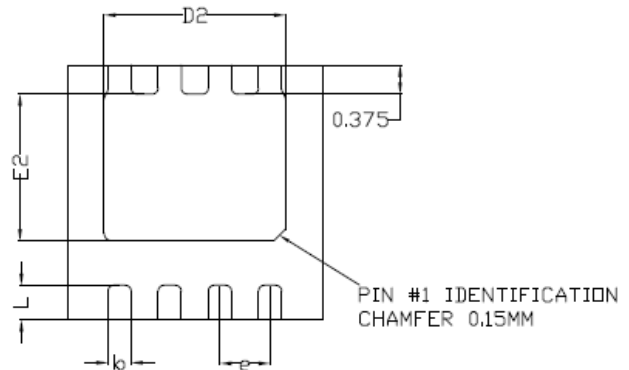


## 8. Package Dimensions

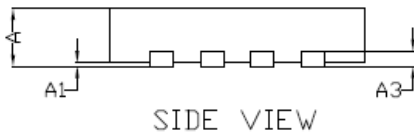
DFN3.3x3.3 - 8L Package



TOP VIEW



BOTTOM VIEW



SIDE VIEW

Lead finish : NiPdAu

Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.7	0.8
A1	0.00	0.05
A3	0.20 REF	
D	3.25	3.35
E	3.25	3.35
D2	2.30	2.40
E2	1.85	1.95
b	0.25	0.35
L	0.35	0.55
e	0.65 BSC	